

SIDC09D60E6

Fast switching diode chip in EMCON-Technology

FEATURES:

- 600V EMCON technology 70 μm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

EUPEC power modules and discrete devices



Applications:

SMPS, resonant applications, drives

Chip Type	V_R	I _F	Die Size	Package	Ordering Code
SIDC09D60E6	600V	20A	3 x 3 mm ²	sawn on foil	Q67050-A4006- A001

MECHANICAL PARAMETER:

Raster size	3 x 3		
Area total / active	9 / 6.7	mm ²	
Anode pad size	2.51 x 2.51		
Thickness	70		
Wafer size	150		
Flat position	180		
Max. possible chips per wafer	1667 pcs		
Passivation frontside	Photoimide		
Anode metallisation	3200 nm AlSiCu		
Cathode metallisation	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding		
Die bond	electrically conductive glue or solder		
Wire bond	AI, ≤500μm		
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm		
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C		



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Continuous forward current limited by T_{jmax}	I _F		20	
Single pulse forward current (depending on wire bond configuration)	I _{FSM}	$t_P = 10 \text{ ms sinusoidal}$ $T_j = 25^{\circ}\text{C}$	80	А
Maximum repetitive forward current limited by T _{jmax}	I _{FRM}		60	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-55+150	°C

Static Electrical Characteristics (tested on chip), T_j =25 °C, unless otherwise specified

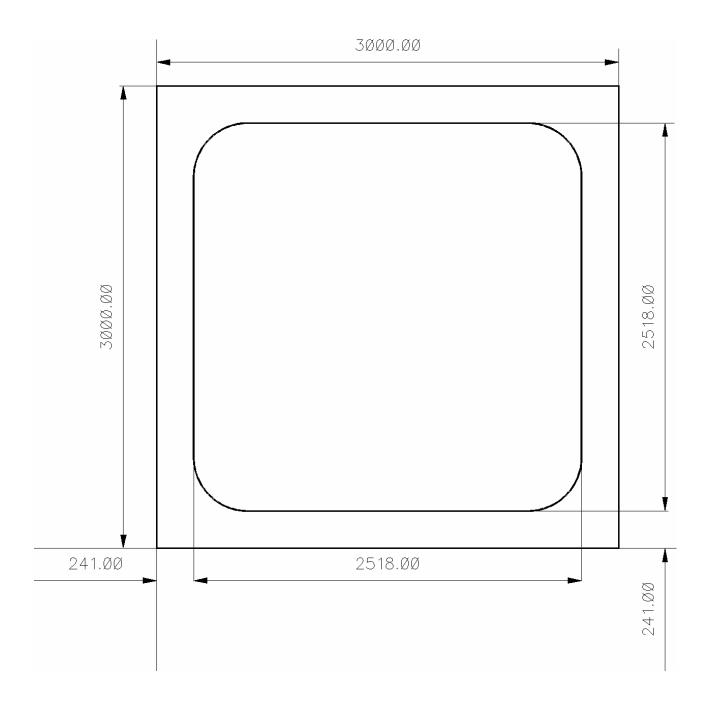
Parameter	Symbol	Condi	Value			Unit	
raiailletei	rameter Symbol		Conditions		Тур.	max.	
Reverse leakage current	I_{R}	V _R =600V	<i>T_j</i> =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V _{Br}	$I_R=3mA$	<i>T_j</i> =25°C	600			V
Forward voltage drop	V_F	I _F =20A	<i>T_j</i> =25 °C	-	1.25	1.7	V

Dynamic Electrical Characteristics, at $T_j = 25$ °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
raiailletei	Syllibol			min.	Тур.	max.	
Reverse recovery time	t _{rr1}	I _F =20A di/dt=700A/ m s	$T_j = 25$ °C		150		ns
	t _{rr2}	$V_R=400V$	$T_j = 125$ °C		200		113
Peak recovery current	I _{RRM1}	I _F =20A	$T_j = 25$ °C		20		Α
	I _{RRM2}	$di/dt=900A/ms$ $V_R=300V$	$T_j = 125$ °C		25]^
Reverse recovery charge	Q _{rr1}	I _F =20A	<i>T_j</i> =25 °C		1.7		μC
	Q _{rr2}	$di/dt=900A/ms$ $V_R=300V$	T _j =125°C		2.7		μΟ



CHIP DRAWING:





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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	INFINEON TECHNOLOGIES / EUPEC	tbd

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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